

ENG2210

Electronic Circuits

Chapter 4 MOSFET

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Disclaimer: Most of the slides are skeletons that will be filled/modified in the lecture. Please do not assume that you can know the material just by reading the slides.

Chapter Objectives

- Learn the physical structure of the MOSFET and how it works.
- How to analyze circuits that contains MOSFET.
- How to obtain linear amplification from a nonlinear MOSFET.
- The three basic ways for connecting a MOSFET to construct amplifiers.
- Practical circuits for MOSFET.

MOSFET– Metal Oxide Semiconductor Field Effect Transistor

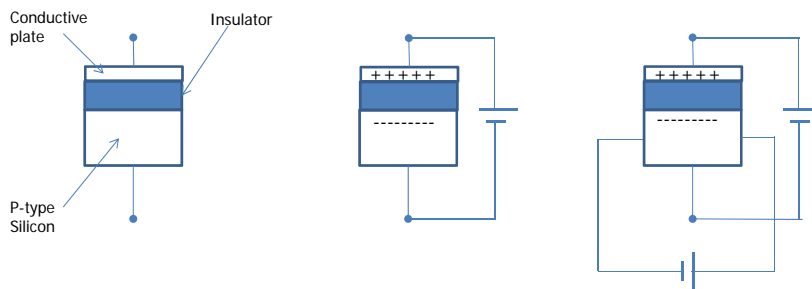
- Transistors (3 terminal devices) diodes are 2 terminal devices – more complicated.
- One terminal usually control the current between the other two terminals.
- Used in digital and analog circuits
- Mainly MOSFET and BJT (vast majority of IC's are MOSFET)
 - Smaller
 - Loss power than BJT – very important –

MOSFET

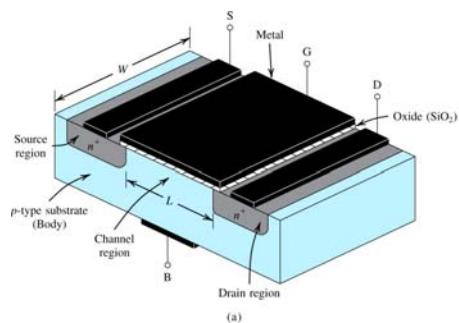
- This is not a course on semiconductor (nor this is a physics course). However, understanding how the device work is very important.

MOSFET

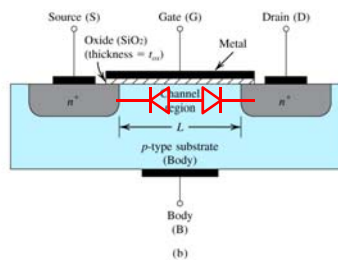
Not a real device, just to explain the idea



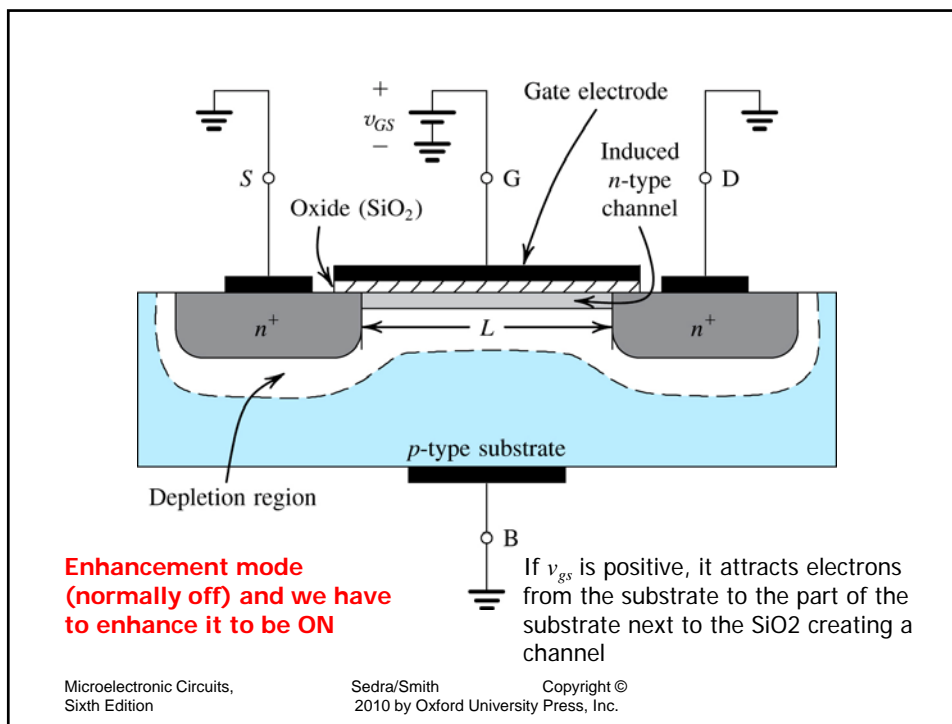
Gate is isolated (SiO_2) no current from gate



No current can flow between source and drain



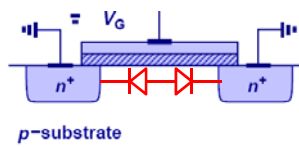
Usually body contact is connected to the source



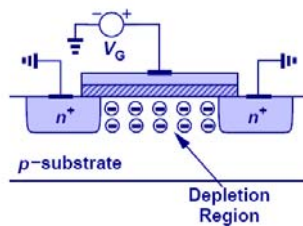
MOSFET Operation

- We start by explaining how things work, then we use mathematics to derive equations.
- Start with n-MOS

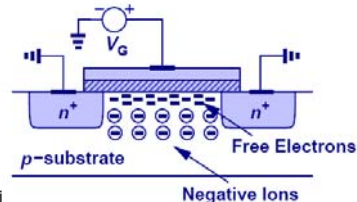
$V_G=0$, because of the back-to-back diodes, no current flows from source to destination



$V_G > 0$, Holes are repelled by the positive gate voltage and leaving behind negative ions forming a depletion region

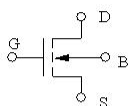


As V_G increases (Threshold voltage), Electrons are attracted to the surface forming a channel where current **might** flow

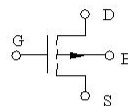


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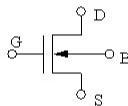
IEEE Standard MOS Transistor Circuit Symbols



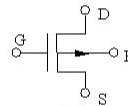
(a) NMOS enhancement-mode device



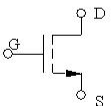
(b) PMOS enhancement-mode device



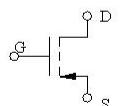
(c) NMOS depletion-mode device



(d) PMOS depletion-mode device



(e) Three-terminal NMOS transistor



(f) Three-terminal PMOS transistor

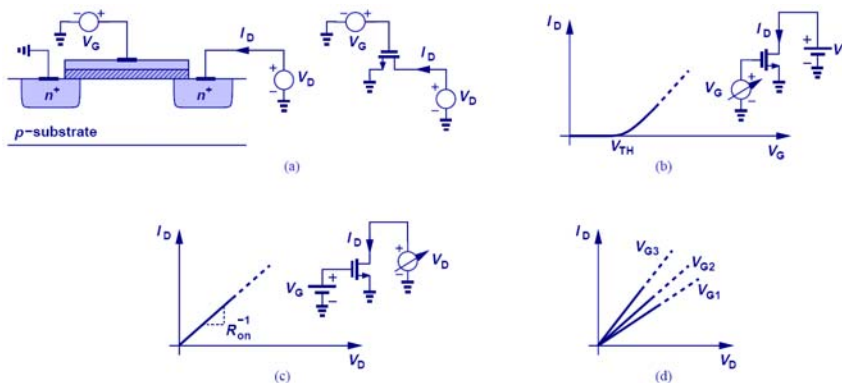
Transistors



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Source: <http://people.seas.harvard.edu/~jones/es154/>

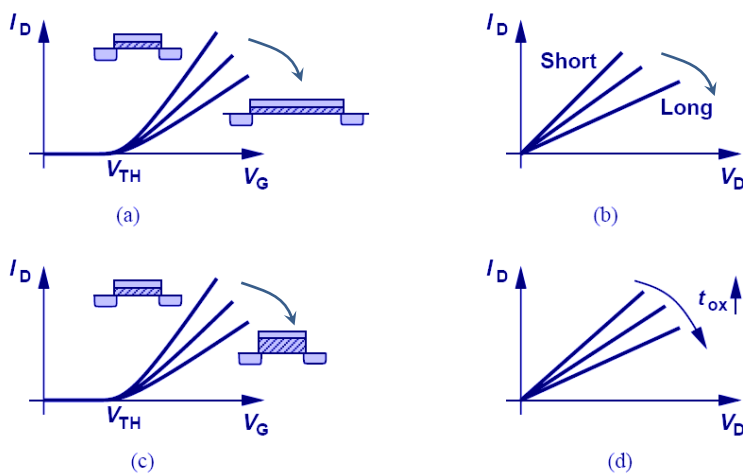
NMOS Characteristics



- We can vary V_G and keeping V_D constant
- Or vary V_D and keeping V_G constant

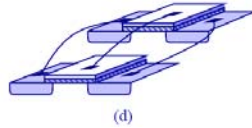
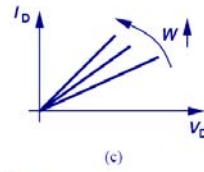
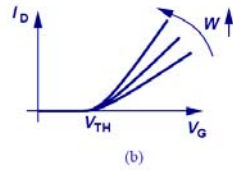
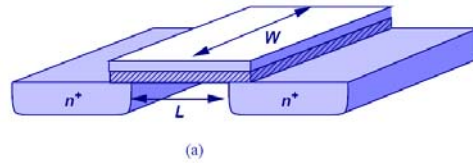
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Effect of L and t_{ox}



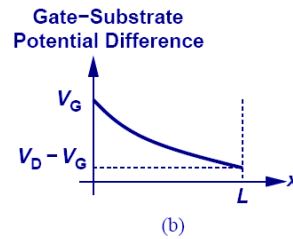
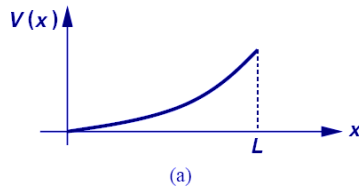
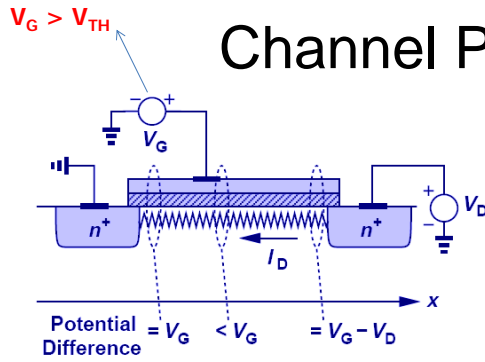
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Effect of W



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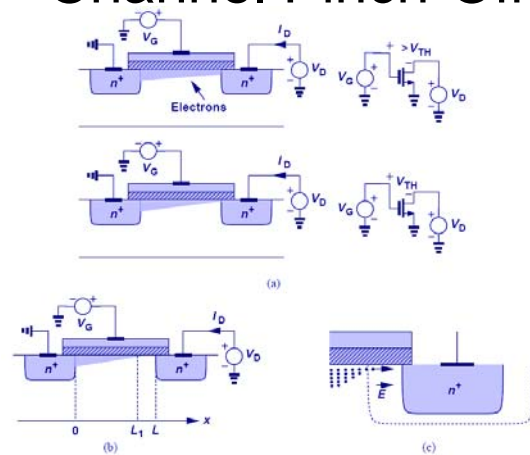
Channel Pinch-off



The channel acts as a resistance, voltage increases from S ($V=0$) to D ($V=V_D$)

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Channel Pinch-Off



- As V_D increases, at some distance x , $V_G - V_D < V_{TH}$ and the channel does not exist anymore.
- Does that mean No current? No, The high electric field in the depletion region carry them through, but V_D does not control the current anymore (constant current source)